

Silicon PNP Power Transistors

2N6317 2N6318

DESCRIPTION

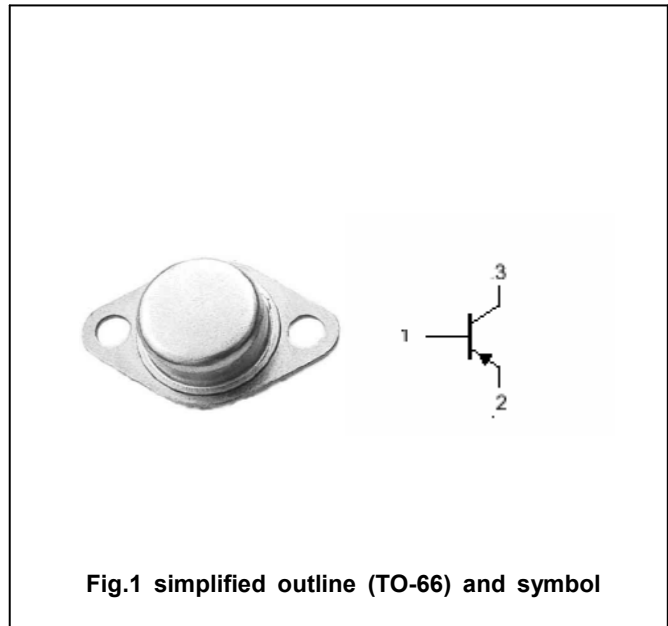
- With TO-66 package
- Low collector saturation voltage
- Complement to type 2N6315/6316

APPLICATIONS

- Designed for general-purpose power amplifier and switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6317	-60	V
		2N6318	-80	
V_{CEO}	Collector-emitter voltage	2N6317	-60	V
		2N6318	-80	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-7	A
I_{CM}	Collector current-peak		-15	A
I_B	Base current		-2	A
P_D	Total Power Dissipation	$T_C = 25 \square$	90	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-65~200	\square

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th j-c}$	Thermal resistance junction to case	1.94	\square/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N6317	I _C =-0.1A ; I _B =0	-60			V
		2N6318		-80			
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-4A; I _B =-0.4 A			-1.0	V	
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-7A; I _B =-1.75A			-2.0	V	
V _{BEsat}	Base-emitter saturation voltage	I _C =-7A; I _B =-1.75A			-2.5	V	
V _{BE}	Base-emitter on voltage	I _C =-2.5A ; V _{CE} =-4V			-1.5	V	
I _{CEO}	Collector cut-off current	2N6317	V _{CE} =-30V; I _B =0			-0.5	mA
		2N6318		V _{CE} =-40V; I _B =0			
I _{CBO}	Collector cut-off current	2N6317	V _{CB} =-60V; I _E =0			-0.25	mA
		2N6318		V _{CB} =-80V; I _E =0			
I _{CEX}	Collector cut-off current	V _{CE} =Rated V _{CE} ; V _{BE(off)} =1.5V T _C =150 °C			-0.25 -2.0	mA	
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1.0	mA	
h _{FE-1}	DC current gain	I _C =-0.5A ; V _{CE} =-4V	35				
h _{FE-2}	DC current gain	I _C =-2.5A ; V _{CE} =-4V	20		100		
h _{FE-3}	DC current gain	I _C =-7A ; V _{CE} =-4V	4				
f _T	Transition frequency	I _C =-0.25A; V _{CE} =-10V; f=1.0MHz	4			MHz	

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PACKAGE OUTLINE

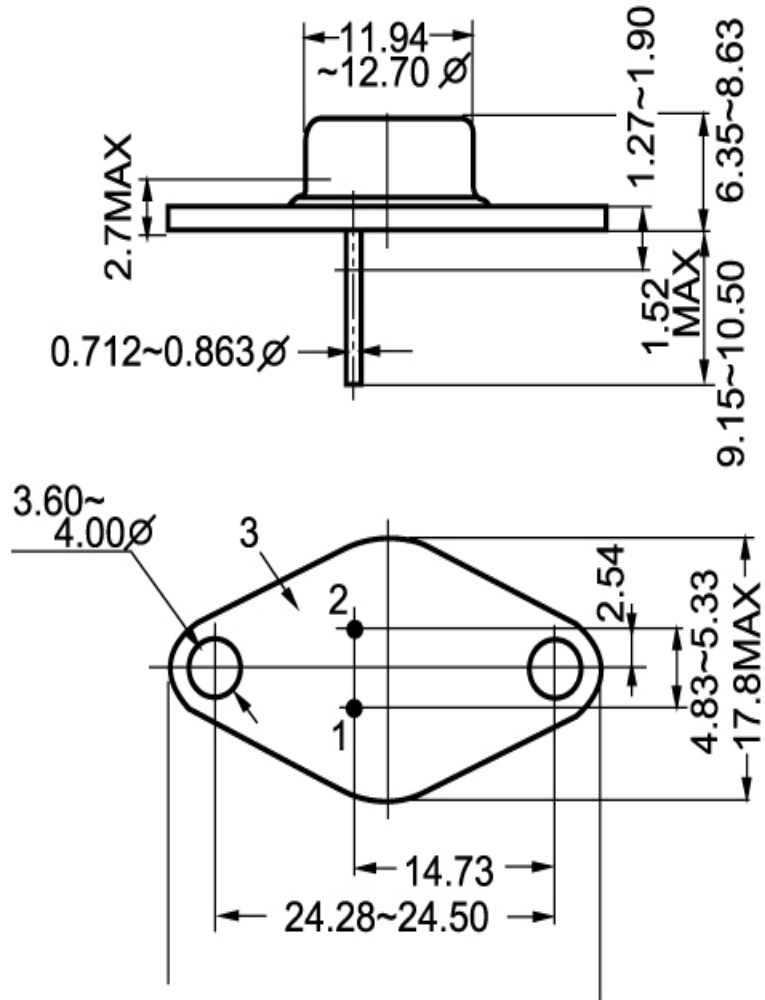


Fig.2 outline dimensions